

Crystal physics

Semiconductors

Electrostriction

$$\frac{\partial P_k}{\partial \sigma_{ij}} = \frac{\partial \epsilon_{ij}}{\partial E_k} = - \left(\frac{\partial^2 G}{\partial E_k \partial \sigma_{ij}} \right) = d_{ijk}$$

$$\epsilon_{ij} = d_{ijk} E_k + Q_{ijkl} E_k E_l + \dots$$

piezoelectricity

Electrostriction

Nonlinear optics

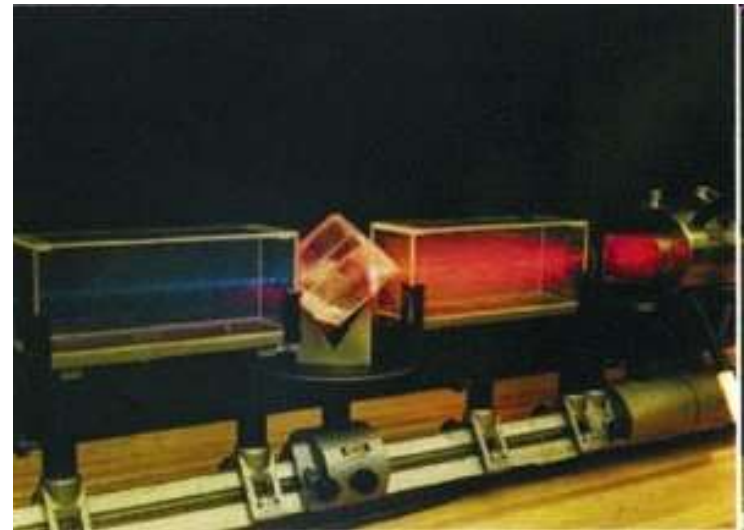
Period doubling crystals

no inversion symmetry

$$P = \chi^{(1)} E + \chi^{(2)} E^2 + \chi^{(3)} E^3 + \dots$$

$$P_i = \frac{-\partial^2 G}{\partial E_i \partial E_j} E_j + \frac{1}{2} \frac{-\partial^3 G}{\partial E_i \partial E_j \partial E_k} E_j E_k + \dots$$

$$\cos^2(\omega t) = \frac{1}{2}(1 + \cos(2\omega t))$$



806 nm light : lithium iodate (LiIO_3)

860 nm light : potassium niobate (KNbO_3)

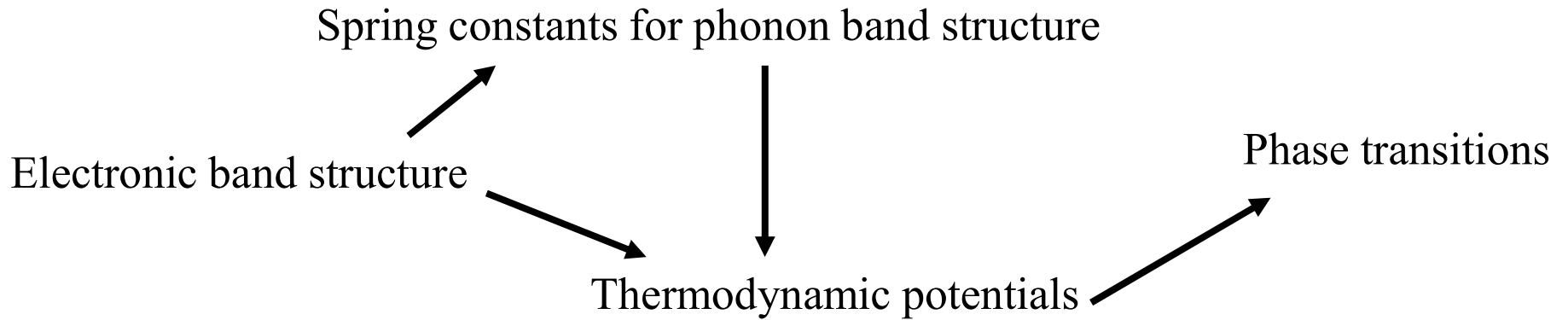
980 nm light : KNbO_3

1064 nm light : monopotassium phosphate (KH_2PO_4 , KDP), lithium triborate (LBO).

1300 nm light : gallium selenide (GaSe)

1319 nm light : KNbO_3 , BBO, KDP, lithium niobate (LiNbO_3), LiIO_3

Thermodynamic properties



total derivative:
$$dG = \left(\frac{\partial G}{\partial T} \right) dT + \left(\frac{\partial G}{\partial \sigma_{ij}} \right) d\sigma_{ij} + \left(\frac{\partial G}{\partial E_k} \right) dE_k + \left(\frac{\partial G}{\partial H_l} \right) dH_l$$

$$\left(\frac{\partial G}{\partial \sigma_{ij}} \right) = -\varepsilon_{ij} \quad \left(\frac{\partial G}{\partial E_k} \right) = -P_k$$

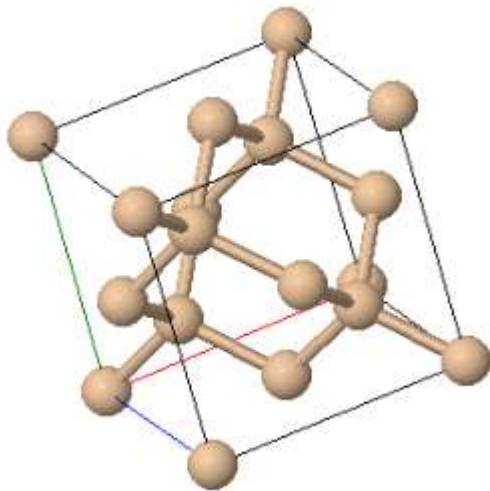
$$\left(\frac{\partial G}{\partial H_l} \right) = -M_l \quad \left(\frac{\partial G}{\partial T} \right) = -S$$

Semiconductors

Silicon

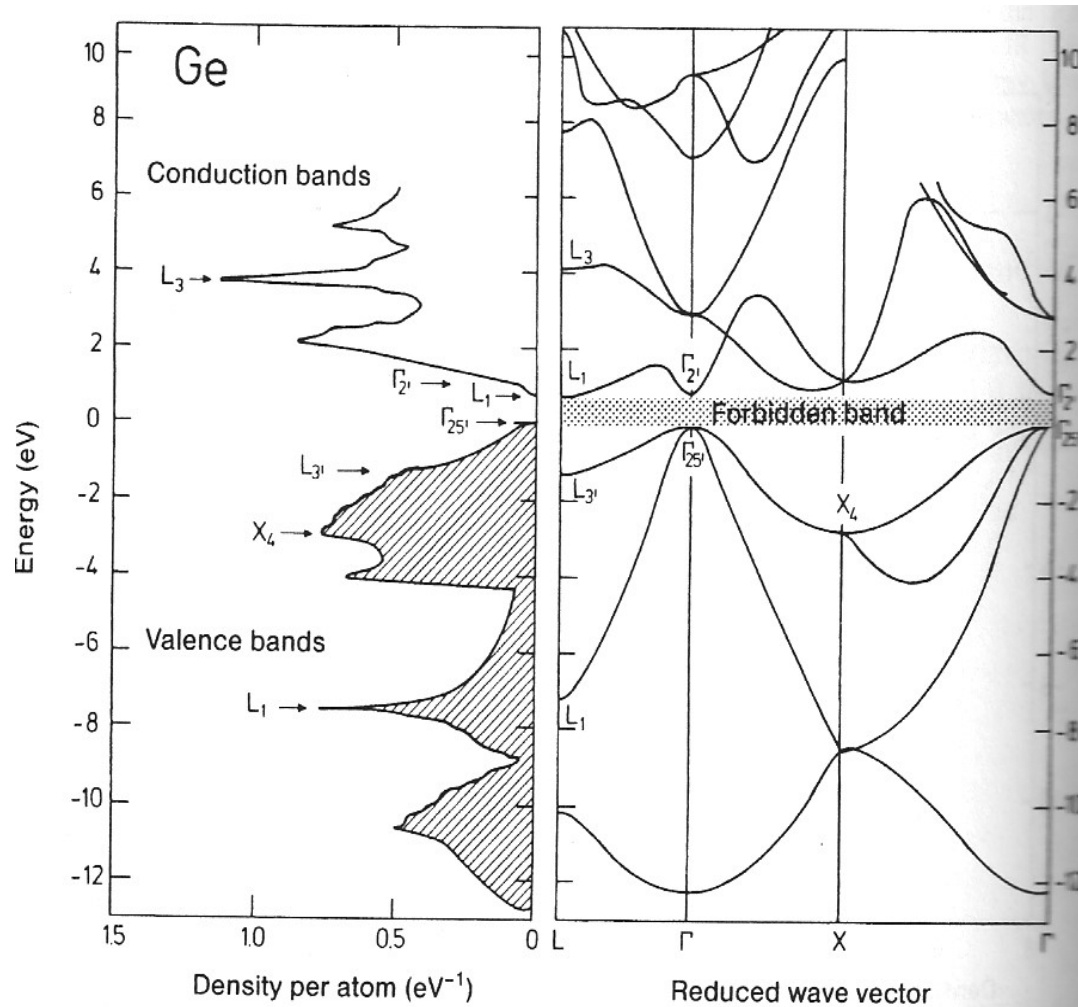
- Important semiconducting material
- 2nd most common element on earth's crust (rocks, sand, glass, concrete)
- Often doped with other elements
- Oxide SiO_2 is a good insulator

2.33		28.086
	Si	14
5.43	$3s^2 3p^2$	
1683	DIA	625



silicon crystal = diamond crystal structure

Semiconductors



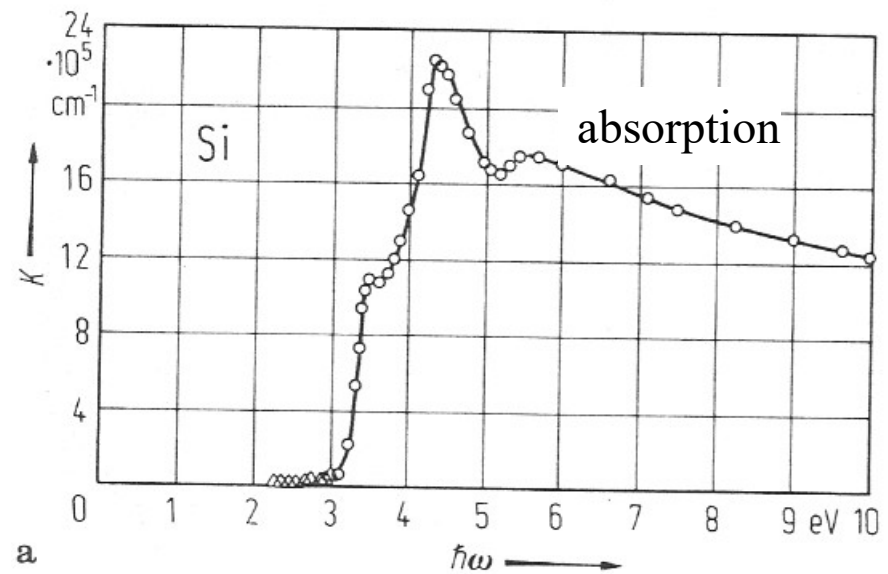
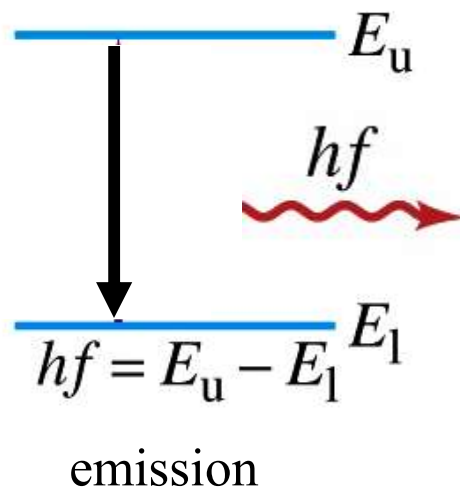
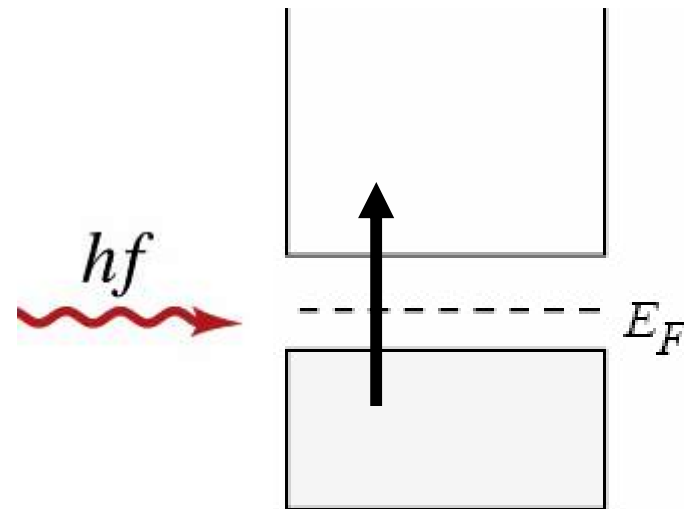
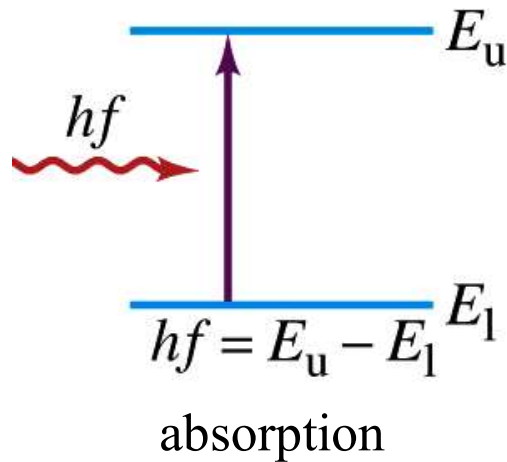
Conduction band

Valence band

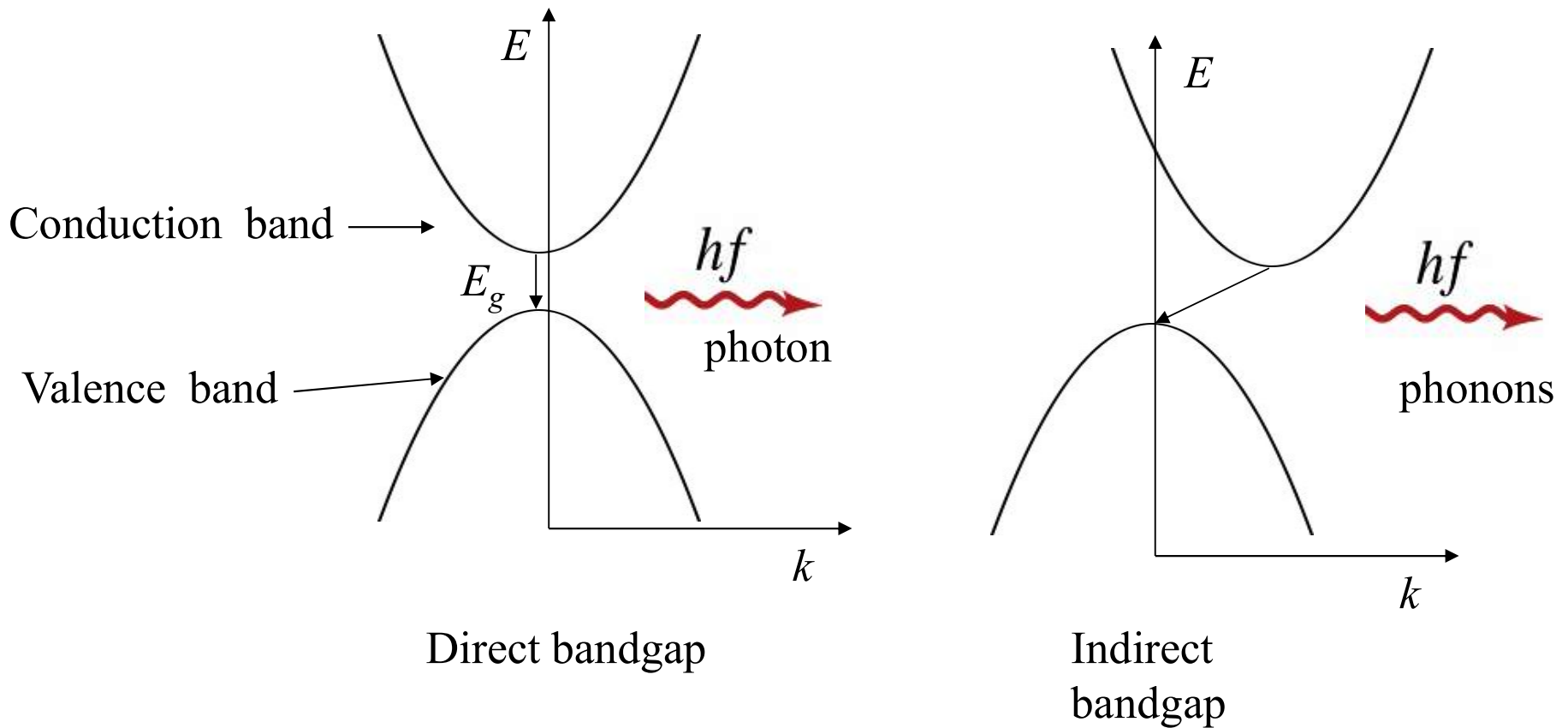
$$n = \int_{-\infty}^{\infty} D(E) f(E) dE$$

From Ibach & Lueth

Absorption and emission of photons

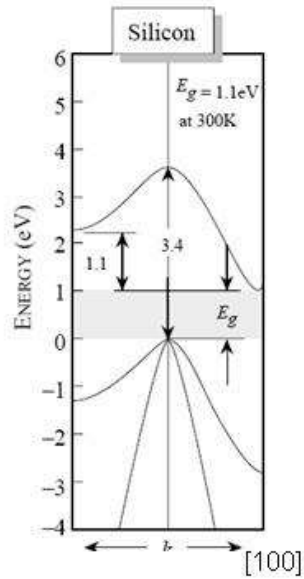


Direct and indirect band gaps

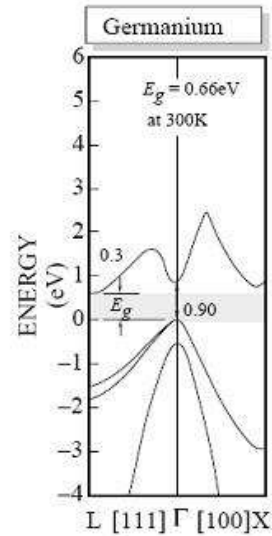


Direct bandgap semiconductors are used for optoelectronics

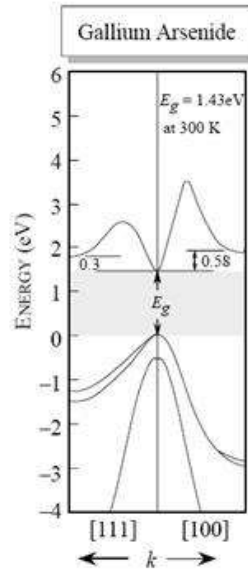
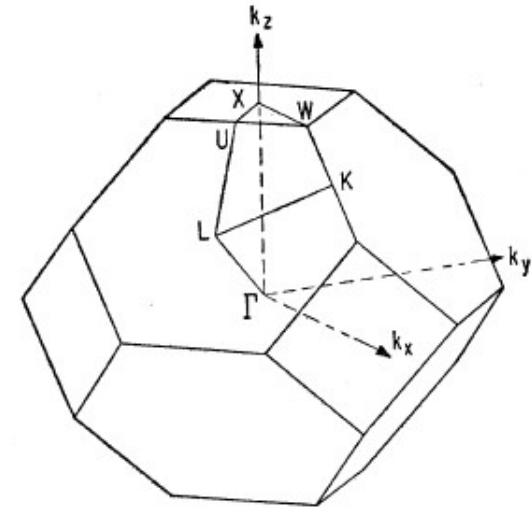
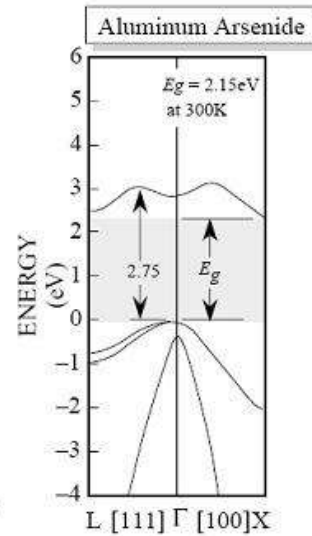
Semiconductors



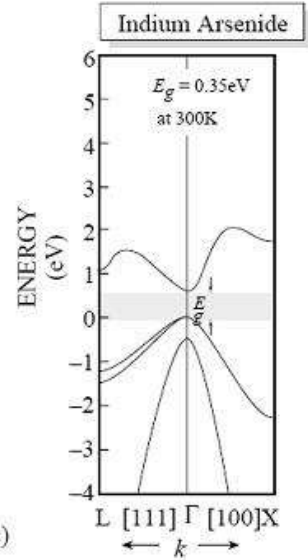
(a)



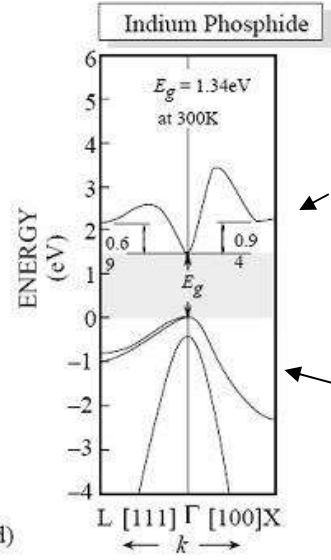
(b)



(c)



(d)



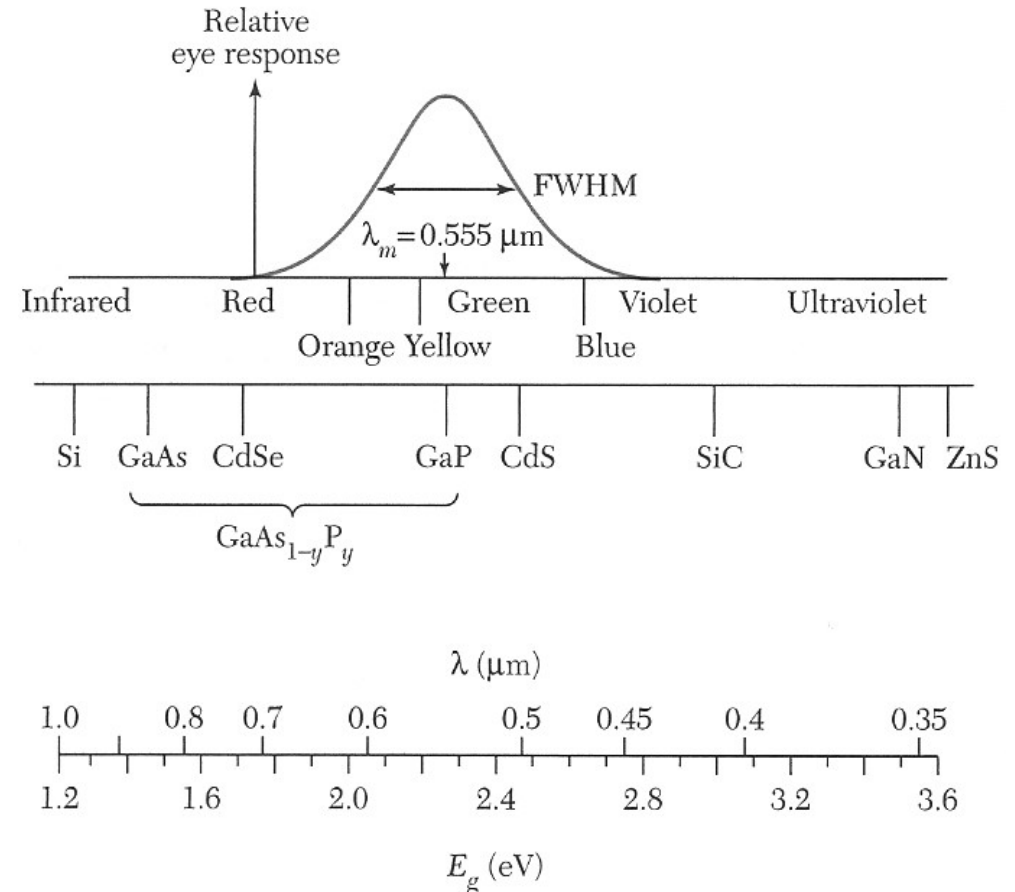
Conduction band

Valence band

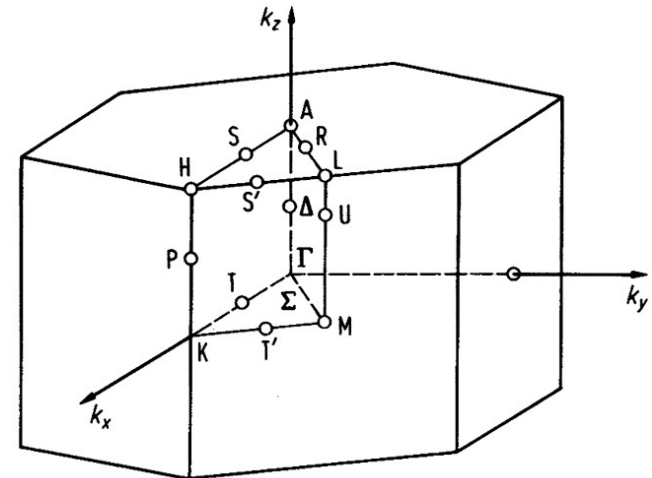
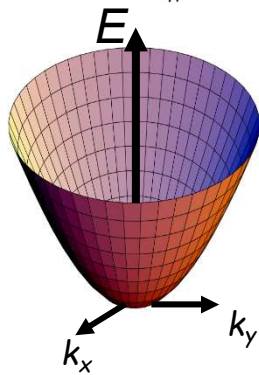
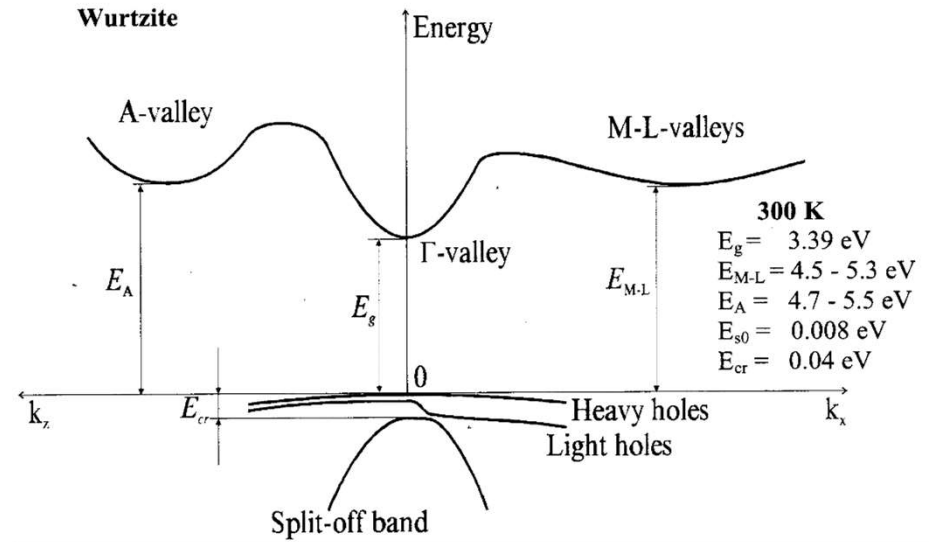
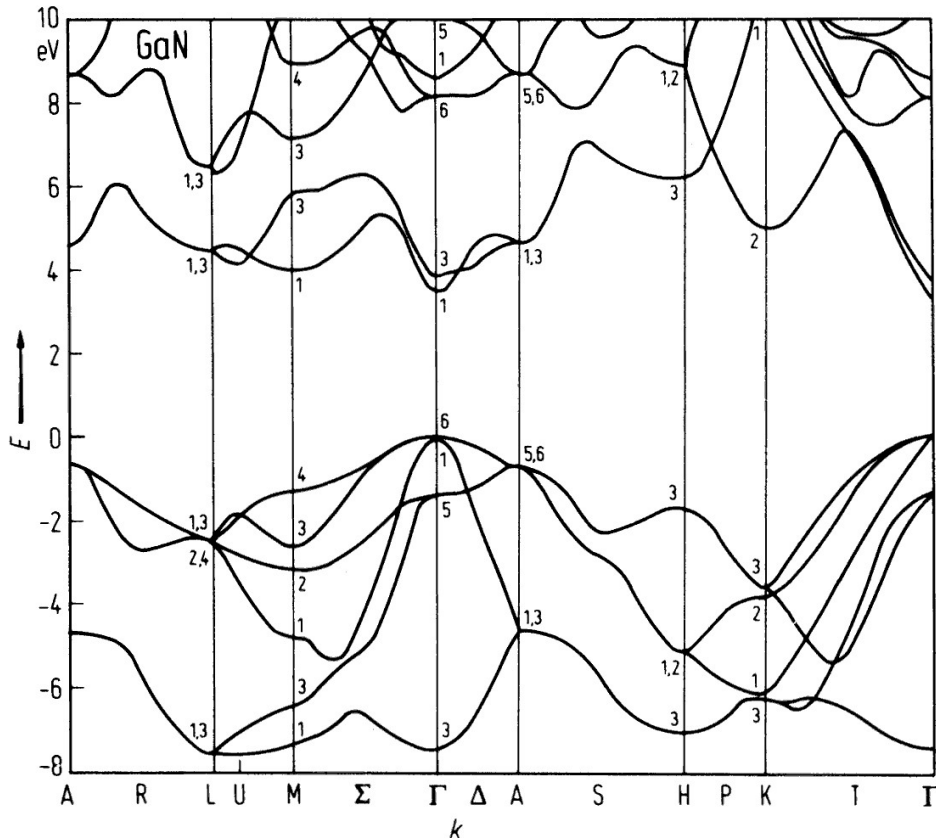
TABLE 1 Common III-V materials used to produce LEDs and their emission wavelengths.

Material	Wavelength (nm)
InAsSbP/InAs	4200
InAs	3800
GaInAsP/GaSb	2000
GaSb	1800
$Ga_xIn_{1-x}As_{1-y}P_y$	1100-1600
$Ga_{0.47}In_{0.53}As$	1550
$Ga_{0.27}In_{0.73}As_{0.63}P_{0.37}$	1300
GaAs:Er, InP:Er	1540
Si:C	1300
GaAs:Yb, InP:Yb	1000
$Al_xGa_{1-x}As:Si$	650-940
GaAs:Si	940
$Al_{0.11}Ga_{0.89}As:Si$	830
$Al_{0.4}Ga_{0.6}As:Si$	650
$GaAs_{0.6}P_{0.4}$	660
$GaAs_{0.4}P_{0.6}$	620
$GaAs_{0.15}P_{0.85}$	590
$(Al_xGa_{1-x})_{0.5}In_{0.5}P$	655
GaP	690
GaP:N	550-570
$Ga_xIn_{1-x}N$	340,430,590
SiC	400-460
BN	260,310,490

Light emitting diodes

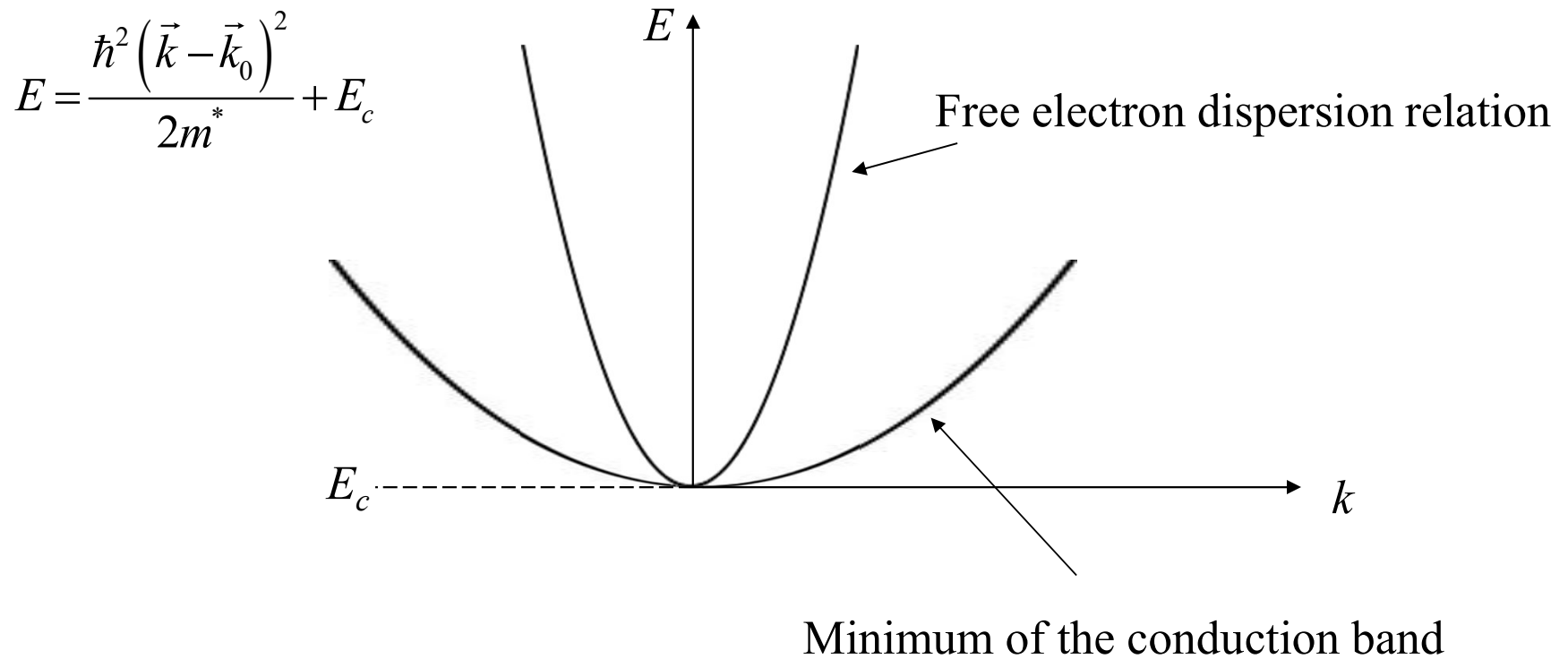


GaN



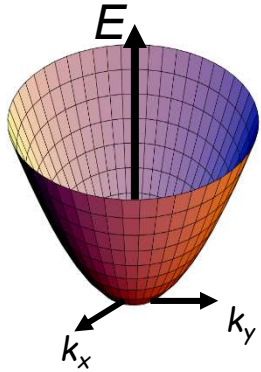
1st Brillouin zone of hcp

Conduction band minimum



Near the conduction band minimum, the bands are approximately parabolic.

Effective mass



$$E = \frac{\hbar^2 (\vec{k} - \vec{k}_0)^2}{2m^*} + E_c$$

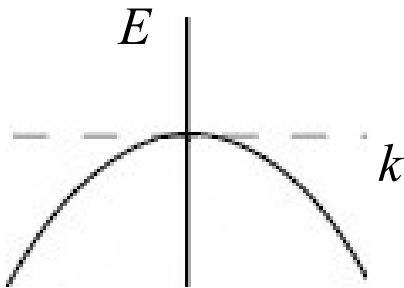
The parabola at the bottom of the conduction band does not have the same curvature as the free-electron dispersion relation. We define an effective mass to characterize the conduction band minimum.

$$m^* = \frac{\hbar^2}{\frac{d^2 E(\vec{k})}{dk_x^2}}$$

This effective mass is used to describe the response of electrons to external forces in the particle picture.

Top of the valence band

In the valence band, the effective mass is negative.



$$m^* = \frac{\hbar^2}{\frac{d^2 E(\vec{k})}{dk_x^2}} < 0$$

Charge carriers in the valence band are positively charged holes.

m_h^* = effective mass of holes

$$m_h^* = \frac{-\hbar^2}{\frac{d^2 E(\vec{k})}{dk_x^2}}$$

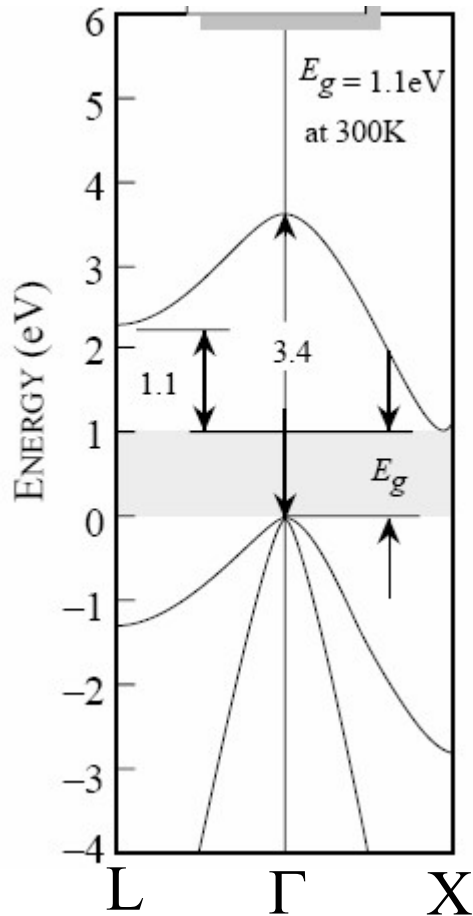
Holes

A completely filled band does not contribute to the current.

$$\begin{aligned}\vec{j} &= \int_{\text{filled states}} -e\vec{v}(\vec{k})D(\vec{k})f(\vec{k})d\vec{k} \\ &= \int_{\text{band}} -e\vec{v}(\vec{k})D(\vec{k})f(\vec{k})d\vec{k} - \int_{\text{empty states}} -e\vec{v}(\vec{k})D(\vec{k})f(\vec{k})d\vec{k} \\ &= \int_{\text{empty states}} e\vec{v}(\vec{k})D(\vec{k})f(\vec{k})d\vec{k}\end{aligned}$$

Holes have a positive charge and a positive mass.

Effective Mass



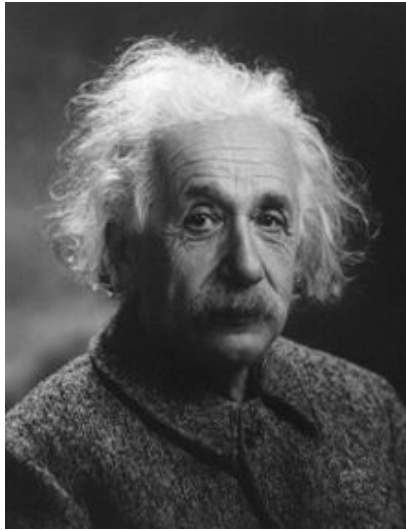
$$E = \frac{\hbar^2 (\vec{k} - \vec{k}_0)^2}{2m^*} + E_c$$

$$m_e^* = \frac{\hbar^2}{\frac{d^2 E}{dk_x^2}}$$

$$E = \frac{-\hbar^2 (\vec{k} - \vec{k}_0)^2}{2m^*} + E_v$$

$$m_h^* = \frac{-\hbar^2}{\frac{d^2 E}{dk_x^2}}$$

Holes



Albert Einstein

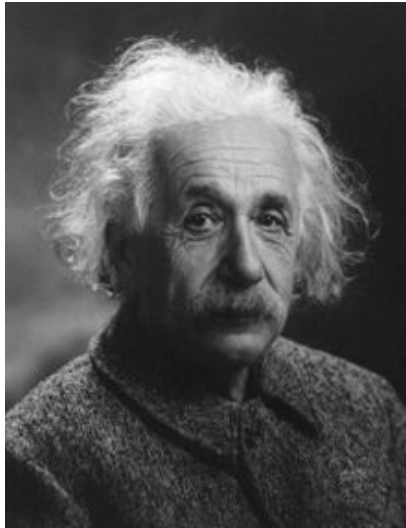


Erwin Schrödinger



Paul Adrien Maurice Dirac

Holes



Albert Einstein



Erwin Schrödinger



Paul Adrien Maurice Dirac

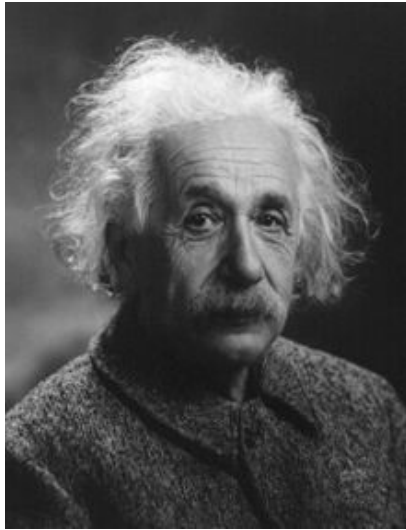
$$\frac{d^2u}{dt^2} = c^2 \frac{d^2u}{dx^2}$$

Wave equation

$$\frac{du}{dt} = k \frac{d^2u}{dx^2}$$

Heat equation

Holes



Albert Einstein



Erwin Schrödinger



Paul Adrien Maurice Dirac

$$\left(\beta mc^2 + \sum_{j=1}^3 \alpha_j p_j c \right) \psi = i\hbar \frac{\partial \psi}{\partial t}$$

Dirac equation

